

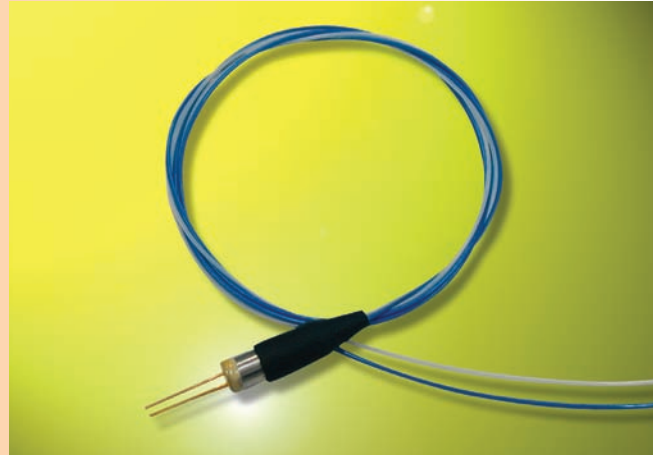
E-TD TAP MONITORING DETECTORS

Features:

- Custom tap ratio available
- Low dark current
- Compact size
- Ultra flat, broadband spectral response

Applications:

- Power monitoring in protecting switches
- Gain monitoring for fiber amplifier
- Power monitoring for OADM system



Performance Specifications:

PARAMETER	SYMBOL	MIN	MAX	UNIT	REMARK
Photodiode Bias Voltage	V _{bias}	-14	-2	V	
Operating Temperature	T _{OP}	0	70	°C	
Storage Temperature	T _{Stg}	-40	85	°C	
Soldering Temperature	T _{Sol}		350	°C	<3sec.

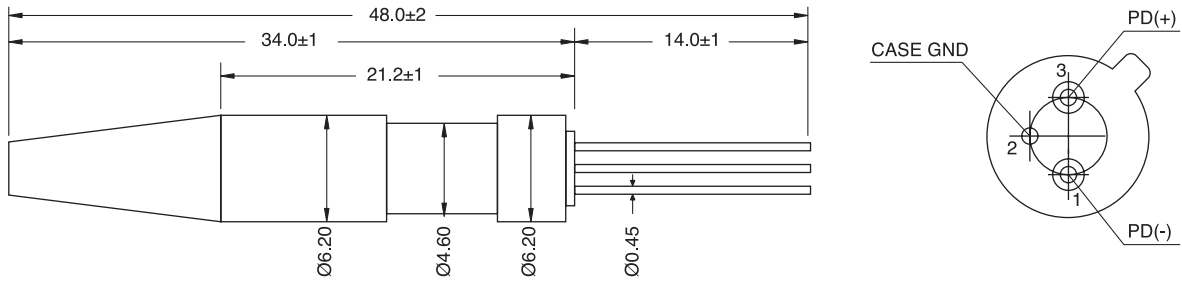
PARAMETER	SYMBOL	MIN	TYP.	MAX	UNIT	REMARK
Detection Range		1100	-	1650	nm	
Dark Current	I _{dark}	-	-	1	nA	
Capacitance	C	-	0.7	0.9	pF	
Bandwidth	BW	2	-	-	GHz	
Responsivity	R	0.8	0.9	-	A/W	λ =1310nm
Breakdown Voltage	V _{BD}	25	55			IR:10uA
Back-reflection	BR	45	-	-	dB	
PDL		-	-	0.1	dB	
PMD		-	-	0.1	ps	
Wavelength flatness				0.2	dB	
Tap Ratio		98:2		95:5		90:10
Optical insertion loss (dB)		0.6		0.8		1.0
Saturation optical power (dBm)		14		10		7
Photodiode tap responsivity (A/W)		0.01-0.04		0.04-0.06		0.08-0.12

Note: Excluding connectors.

TAP MONITORING DETECTORS

Diagram & Dimension:

Unit: mm



Ordering Information:

E - TD - 3PA - - - - - - BMF

Speed								
PIN Type								
Fiber Type								
A	SMF							
Wavelength								
13	1310 nm							
15	1550 nm							
35	1310 & 1550 nm							
Tap Ratio								
02	98 : 2							
05	95 : 5							
10	90 : 10							
Fiber Length								
0001	1 meter							
X150	150cm							
XXXX	Please specify							
Connector Type								
SC	SC type							
ST	ST type							
NC	None							
XX	Others							
Checking Number								